

**AMENDMENTS TO THE CLAIMS:**

1. (Cancelled)

2. (Cancelled)

3. (Cancelled)

4. (Cancelled)

5. (Cancelled)

6. (Cancelled)

7. (Cancelled)

8. (Cancelled)

9. (Cancelled)

10. (Cancelled)

11. (Cancelled)

12. (Cancelled)

13. (Cancelled)

14. (Cancelled)

15. (Cancelled) :

16. (Cancelled)

17. (Currently Amended) A damascene interconnection comprising:  
an interconnection trench formed in an insulating film and a pad trench  
communicating therewith;

a protrusion formed by a portion not removed of said insulating film in said pad  
trench to decrease a substantial opening area of said pad trench; ~~and~~  
a conductive film buried in said interconnection trench and said pad trench; and  
a further conductive film;

wherein the protrusion is formed as a plurality of insulating protrusions within the pad  
trench, the plurality of insulating protrusions reducing the overall volume of the conductive  
film of the pad trench and increasing the electrical resistance of the conductive film of the  
pad trench, the further conductive film being formed below the insulating film and the  
plurality of insulating protrusions; and wherein the damascene interconnection further  
includes a plurality of contact holes formed within the pad trench, each contact hole of the  
plurality of contact holes being positioned near at least one insulating protrusion of the  
plurality of insulating protrusions, at least some of the contact holes being situated between  
adjacent insulating protrusions, each contact hole of the plurality of contact holes being  
electrically connected between the conductive film of the pad trench and the further  
conductive film formed below the insulating film to define an electrical connection, the  
electrical connection between the conductive film of the pad trench and the further  
conductive film formed below the insulating film increasing the effective volume of the  
conductive film of the pad trench, thereby decreasing the overall electrical resistance of the  
conductive film of the pad trench.

18. (Previously Amended) A semiconductor device, comprising:  
a semiconductor substrate;  
an insulating film formed on said semiconductor substrate;  
an interconnection trench formed on said insulating film and communicating with a  
semiconductor element;  
a pad trench formed on said insulating film and communicating with said  
interconnection trench;  
a protrusion formed by a portion not removed of said insulating film in said pad  
trench and reducing a substantial opening area of said pad trench;  
a conductive film buried in said interconnection trench and said pad trench; and

a further conductive film formed below said insulating film;

wherein the protrusion is formed as a plurality of insulating protrusions within the pad trench, the plurality of insulating protrusions reducing the overall volume of the conductive film of the pad trench and increasing the electrical resistance of the conductive film of the pad trench, the further conductive film being formed below the insulating film and the plurality of insulating protrusions; and wherein the semiconductor device further includes a plurality of contact holes formed within the pad trench, each contact hole of the plurality of contact holes being positioned near at least one insulating protrusion of the plurality of insulating protrusions, at least some of the contact holes being situated between adjacent insulating protrusions, each contact hole of the plurality of contact holes being electrically connected between the conductive film of the pad trench and the further conductive film formed below the insulating film to define an electrical connection, the electrical connection between the conductive film of the pad trench and the further conductive film formed below the insulating film increasing the effective volume of the conductive film of the pad trench, thereby decreasing the overall electrical resistance of the conductive film of the pad trench.